FLAT-BASE TYPE INSULATED PACKAGE

PM50RL1A120



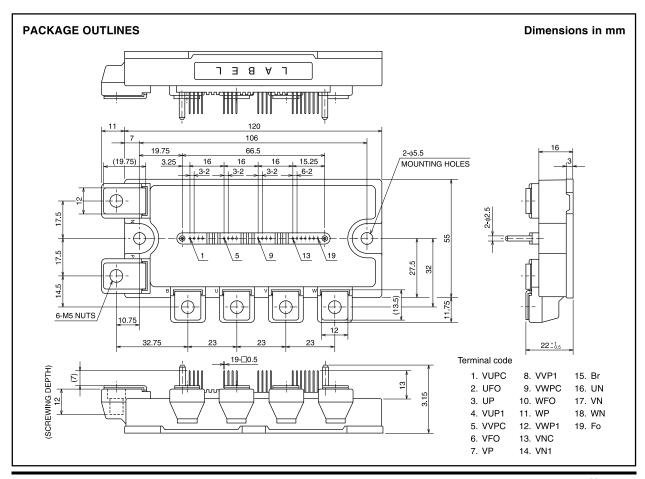
FEATURE

Inverter + Brake + Drive & Protection IC

- a) Adopting new 5th generation Full-Gate CSTBTTM chip
- b) The over-temperature protection which detects the chip surface temperature of $\mathsf{CSTBT^{TM}}$ is adopted.
- c) Error output signal is possible from all each protection upper and lower arm of IPM.
- d) Compatible L-series package.
 - 3φ 50A, 1200V Current-sense and temperature sense IGBT type inverter
 - Monolithic gate drive & protection logic
 - Detection, protection & status indication circuits for, shortcircuit, over-temperature & under-voltage (P-Fo available from upper arm devices)
 - UL Recognized

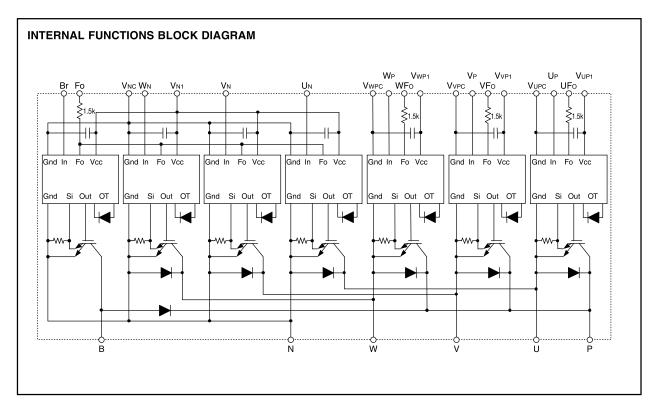
APPLICATION

General purpose inverter, servo drives and other motor controls





FLAT-BASE TYPE INSULATED PACKAGE



MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V	1200	٧
±ΙC	Collector Current	$Tc = 25^{\circ}C$ (Note-1)	50	Α
±ICP	Collector Current (Peak)	Tc = 25°C	100	Α
Pc	Collector Dissipation	$Tc = 25^{\circ}C$ (Note-1)	462	W
Tj	Junction Temperature		−20 ~ +150	°C

^{*:} To measurement point is just under the chip.

BRAKE PART

Symbol	Parameter	Condition	Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V	1200	V
Ic	Collector Current	$Tc = 25^{\circ}C$ (Note-1)	25	Α
ICP	Collector Current (Peak)	Tc = 25°C	50	Α
Pc	Collector Dissipation	$Tc = 25^{\circ}C$ (Note-1)	320	W
lF	FWDi Forward Current	Tc = 25°C	25	Α
VR(DC)	FWDi Rated DC Reverse Voltage	Tc = 25°C	1200	V
Tj	Junction Temperature		−20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Supply Voltage	Applied between: Vup1-Vupc, Vvp1-Vvpc Vwp1-Vwpc, Vv1-Vvpc	20	V
VCIN	Input Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC UN • VN • WN • Br-VNC	20	V
VFO	Fault Output Supply Voltage	Applied between : UFO-VUPC, VFO-VVPC, WFO-VWPC FO-VNC	20	٧
lfo	Fault Output Current	Sink current at UFO, VFO, WFO, Fo terminals	20	mA



FLAT-BASE TYPE INSULATED PACKAGE

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	V _D = 13.5 ~ 16.5V Inverter Part, T _j = +125°C Start	800	V
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	1000	V
Tstg	Storage Temperature		−40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

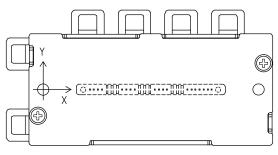
THERMAL RESISTANCES

		Condition					
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
Rth(j-c)Q	Junction to case Thermal	Inverter IGBT part (per 1 element)	(Note-1)	_	_	0.27	
Rth(j-c)F		Inverter FWDi part (per 1 element)	(Note-1)	_	_	0.47	
Rth(j-c)Q	Resistances	Brake IGBT part	(Note-1)		_	0.39	°C/W
Rth(j-c)F		Brake FWDi upper part	(Note-1)	_	_	0.67	1 -0/00
Rth(c-f) Cont	Contact Thermal Resistance	Case to fin, (per 1 module)		,		0.000	1
	Contact Thermal Resistance	Thermal grease applied	(Note-1)		_	0.038	

^{*} If you use this value, Rth(f-a) should be measured just under the chips.

(Note-1) Tc (under the chip) measurement point is below.

(Note-1) Tc (under the chip) measurement point is below.									(un	it : mm)					
	arm	U	P	V	Р	W	/P	U	N	V	N	W	'N	В	R
axis		IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	Di
Х		28.6	28.6	65.4	65.4	87.4	87.4	38.6	38.6	54.6	54.6	76.6	76.6	18.0	19.3
Y		-84	0.2	-84	0.2	-8 4	0.2	6.8	-18	6.8	-1.8	6.8	-18	-8.9	5.0



Bottom view

ELECTRICAL CHARACTERISTICS (Tj = 25°C, unless otherwise noted)

INVERTER PART

	5 .	Condition				Unit		
Symbol	Parameter	Condition	l		Min.	Тур.	Max.	Offic
Vor.	Collector-Emitter Saturation	VD = 15V, IC = 50A		Tj = 25°C	_	1.65	2.15	V
VCE(sat)	Voltage	VCIN = 0V, Pulsed (F	Fig. 1)	Tj = 125°C	_	1.85	2.35	\ \
VEC	FWDi Forward Voltage	-lc = 50A, VD = 15V, VCIN = 15V	/	(Fig. 2)	_	2.3	3.3	V
ton		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\			0.3	0.8	2.0	
trr		VD = 15V, VCIN = 0V↔15V			_	0.3	8.0	
tc(on)	Switching Time	Vcc = 600V, Ic = 50A			_	0.4	1.0	μs
toff		Tj = 125°C		(Fig. 0.4)	_	1.2	2.8	
tc(off)		Inductive Load		(Fig. 3,4)	_	0.4	1.2	
loss	Collector-Emitter Cutoff	Vos Vos Vo 45V (6	=: =\	Tj = 25°C	_	_	1	0
ICES	Current	VCE = VCES, VD = 15V (F	(Fig. 5)	Tj = 125°C		_	10	mA



FLAT-BASE TYPE INSULATED PACKAGE

BRAKE PART

0	D	Condition		1.1				
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit	
1/05/ "	Collector-Emitter Saturation	VD = 15V, IC = 25A	Tj = 25°C	_	1.65	2.15	v	
VCE(sat)	Voltage	VCIN = 0V, Pulsed (Fig. 1)	Tj = 125°C	_	1.85	2.35	v	
VEC	FWDi Forward Voltage	-IC = 25A, VCIN = 15V, VD = 15V	(Fig. 2)	_	2.3	3.3	V	
ICES	Collector-Emitter Cutoff	VCE = VCES, VD = 15V (Fig. 5)	Tj = 25°C	_	_	1	A	
	Current	VCE = VCES, VD = 15V (Fig. 5)	Tj = 125°C	_	_	10	mA	

CONTROL PART

Cumahal	Demonstra	O and the an			Limits		Unit
Symbol	Parameter	Condition		Min.	Тур.	Max.	
ID	Circuit Current	VD = 15V, VCIN = 15V	Vn1-Vnc	_	8	16	mA
10	Circuit Current	VD = 13V, VCIN = 13V	V*P1-V*PC	_	2	4	IIIA
Vth(ON)	Input ON Threshold Voltage	Applied between: UP-VUPC, VP-VVPC, V	WP-VWPC	1.2	1.5	1.8	V
Vth(OFF)	Input OFF Threshold Voltage	Un • Vn • Wn • Br-Vn	NC	1.7	2.0	2.3	V
sc	Short Circuit Trip Level	$-20 \le T_i \le 125^{\circ}C$, $VD = 15V$ (Fig. 3.6)	Inverter part	100	_	_	Α
30	· ·	-20 ≤ 1] ≤ 125 C, VD = 15V (Fig. 3,0)	Brake part	50	_	_	_ ^ _
toff(SC)	Short Circuit Current Delay Time	VD = 15V	(Fig. 3,6)	_	0.2	_	μs
ОТ	Over Temperature Protection	Detect Temperature of ICPT chin	Trip level	135	_	_	°C
OT(hys)	Over Temperature Protection	Detect Temperature of IGBT chip	Hysteresis	_	20	_	
UV	Supply Circuit Under-Voltage	–20 ≤ Tj ≤ 125°C	Trip level	11.5	12.0	12.5	V
UVr	Protection	-20 \(\) 1 \(\) \(\) 1 \(\) \(\	Reset level	_	12.5	_	1 '
IFO(H)	Fault Output Current	VD = 15V, VCIN = 15V	(Note-2)	_	_	0.01	mA
IFO(L)	Taun Output Current	VD = 13V, VOIN = 13V	(14016-2)	_	10	15	
tFO	Minimum Fault Output Pulse Width	VD = 15V	(Note-2)	1.0	1.8	_	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

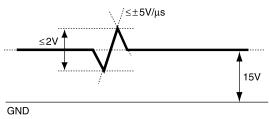
MECHANICAL RATINGS AND CHARACTERISTICS

Condition				Unit			
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
	Mounting torque	Mounting part so	crew : M5	2.5	3.0	3.5	N•m
_		Main terminal part so	crew : M5	2.5	3.0	3.5	N•m
_	Weight			_	380	_	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 800	V
VD	Control Supply Voltage	Applied between : VuP1-VuPC, VvP1-VvPC VwP1-VwPC, Vn1-VnC (Note-3)	15.0 ± 1.5	٧
VCIN(ON)	Input ON Voltage	Applied between: UP-VUPC, VP-VVPC, WP-VWPC	≤ 0.8	
VCIN(OFF)	Input OFF Voltage	Un • Vn • Wn • Br-Vnc	≥ 9.0]
fpwm	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 2.5	μs

(Note-3) With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak



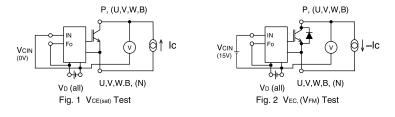


FLAT-BASE TYPE INSULATED PACKAGE

PRECAUTIONS FOR TESTING

- Before applying any control supply voltage (VD), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
 After this, the specified ON and OFF level setting for each input signal should be done.
- 2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above VCEs rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)



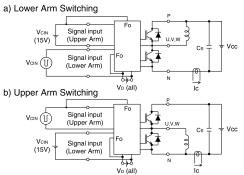


Fig. 3 Switching Time and SC Test Circuit

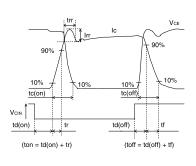


Fig. 4 Switching Time Test Waveform

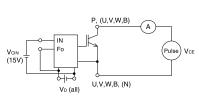


Fig. 5 Ices Test

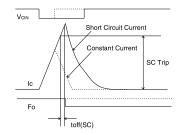
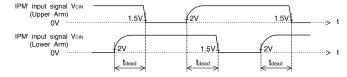


Fig. 6 SC Test Waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example



FLAT-BASE TYPE INSULATED PACKAGE

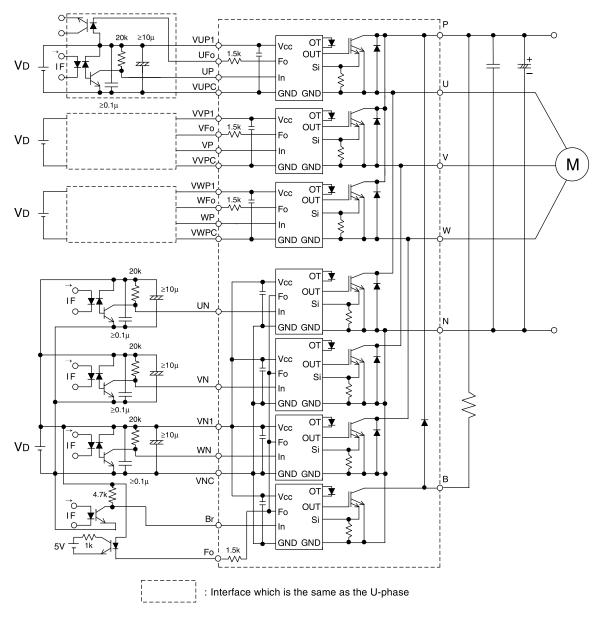


Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION;

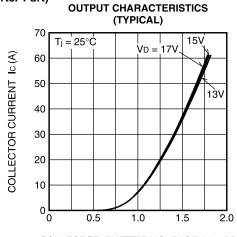
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: tPLH, tPHL ≤ 0.8μs, Use High CMR type.
- ●Slow switching opto-coupler: CTR > 100%
- Use 4 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- •Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.



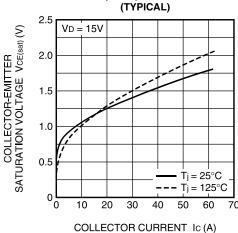
FLAT-BASE TYPE INSULATED PACKAGE

PERFORMANCE CURVES

(Inverter Part)

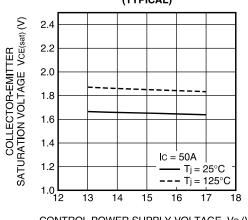


COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS



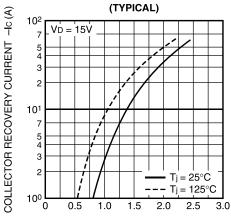
COLLECTOR-EMITTER VOLTAGE VCE (V)

COLLECTOR-EMITTER SATURATION VOLTAGE (VS. VD) CHARACTERISTICS (TYPICAL)



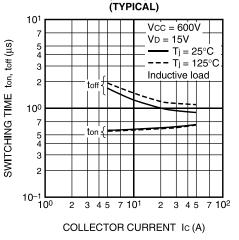
CONTROL POWER SUPPLY VOLTAGE VD (V)

DIODE FORWARD CHARACTERISTICS

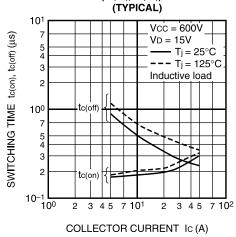


EMITTER-COLLECTOR VOLTAGE VEC (V)

SWITCHING TIME (ton, toff) CHARACTERISTICS



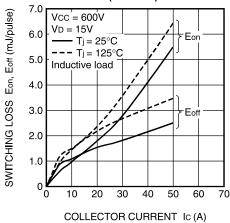
SWITCHING TIME (tc(on), tc(off)) CHARACTERISTICS



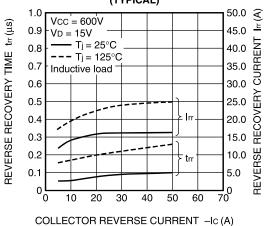


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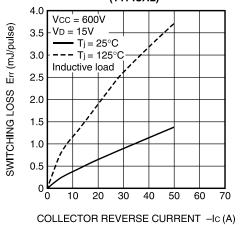
SWITCHING LOSS CHARACTERISTICS (TYPICAL)



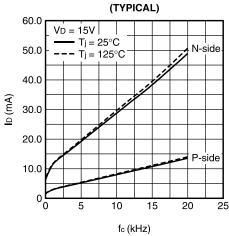
DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



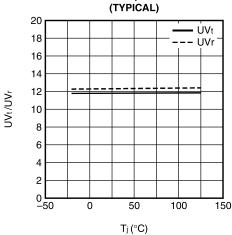
SWITCHING RECOVERY LOSS CHARACTERISTICS (TYPICAL)



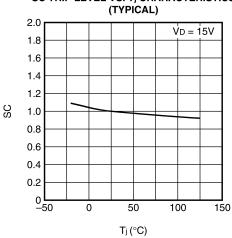
ID VS. fc CHARACTERISTICS



UV TRIP LEVEL VS. Tj CHARACTERISTICS

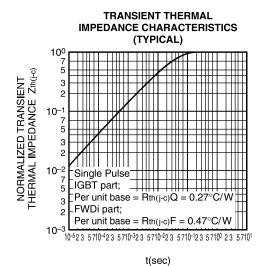


SC TRIP LEVEL VS. Tj CHARACTERISTICS

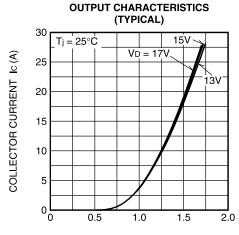




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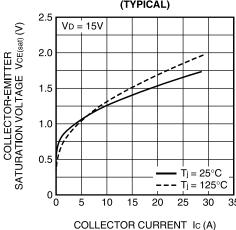


(Brake Part)

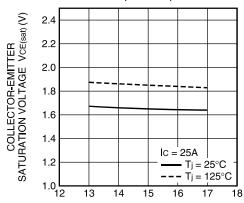


COLLECTOR-EMITTER VOLTAGE VCE (V)

COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS (TYPICAL)

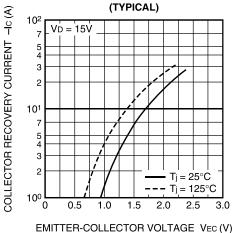


COLLECTOR-EMITTER SATURATION VOLTAGE (VS. VD) CHARACTERISTICS (TYPICAL)

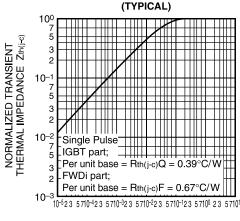


CONTROL POWER SUPPLY VOLTAGE VD (V)

DIODE FORWARD CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



t(sec)



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